

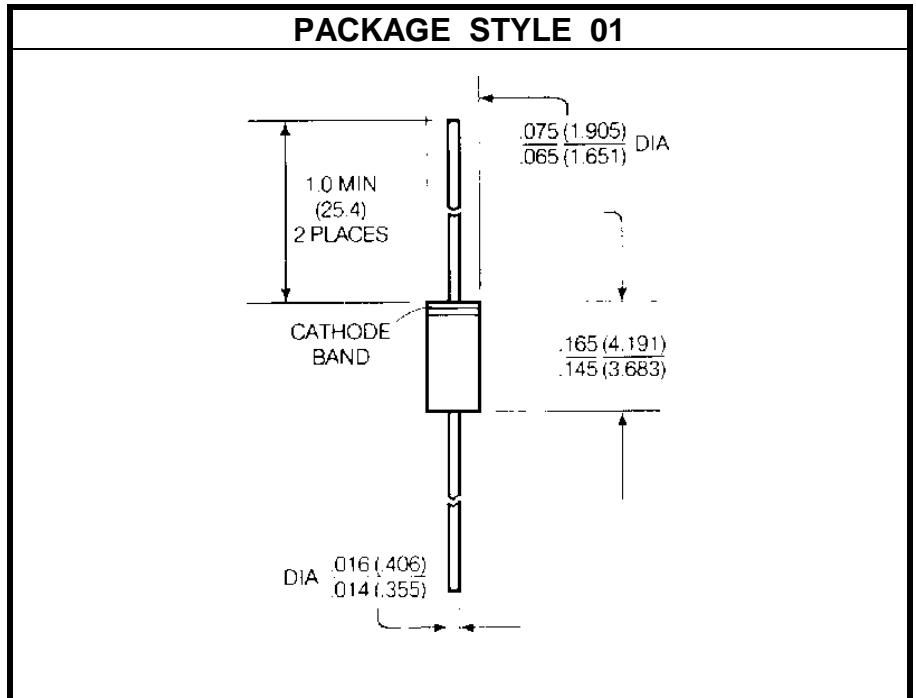
SILICON PIN DIODE

DESCRIPTION:

The **AP1000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I	100 mA
V	100 V
P_{DISS}	250 mW @ T _A = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	30 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V _B	I _R = 10 μA	100			V
C _J	V _R = 50 V V _R = 40 V			0.15	pF
C _P			0.10		pF
L _S			1.0		nH
R _S	I _F = 10 mA			1.5	Ohms
T _L	I _F = 10 mA I _R = 6.0 mA		100		nS
T _{rr}	I _F = 20 mA I _R = 100 mA @ 90%		20		nS
I-REGION			12		μM